



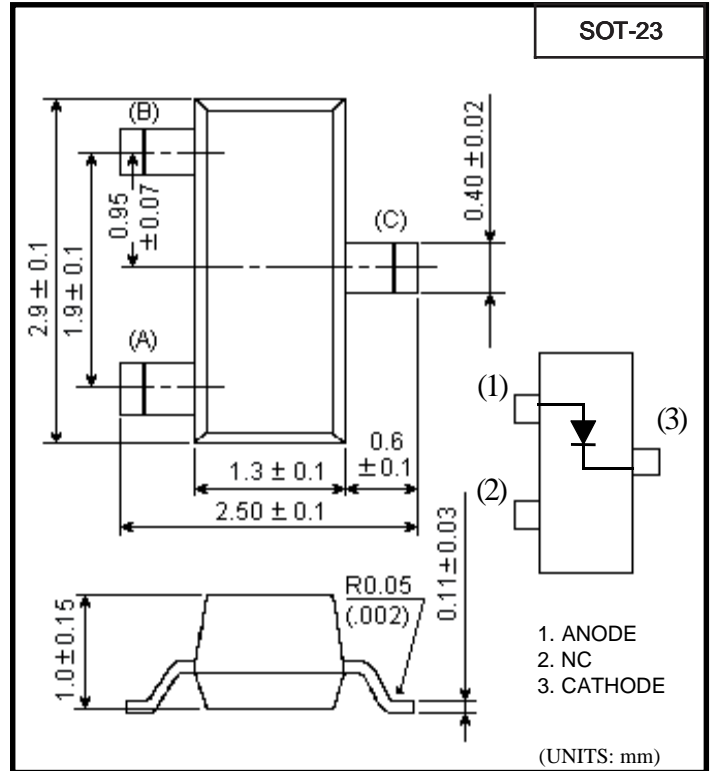
SURFACE MOUNT 1N4150 DIODE

Absolute Maximum Ratings (Ta=25°C)

| ITEMS | SYMBOL | RATINGS | UNIT |
|------------------------------|--------|------------|------|
| Reverse Voltage | VR | 50 | V |
| Reverse Recovery Time | trr | 6 | ns |
| Forward Voltage @ If = 50 mA | VF | 0.86 | V |
| Forward Current | IF | 300 | mA |
| Junction Temp. | Tj | -55 to 150 | °C |
| Storage Temp. | Tstg | -55 to 150 | °C |

Mechanical Data

| ITEMS | MATERIALS |
|-------------|----------------|
| Package | SOT-23 |
| Lead Frame | 42 Alloy |
| Lead Finish | Solder Plating |
| Bond Wire | Au |
| Mold Resin | Epoxy |
| Chip | Silicon |



Electrical Characteristics (Ta=25°C)

| RATINGS | SYMBOL | RATINGS | UNIT |
|---|--------|---------|------|
| Reverse Voltage IR= 100uA | VR | 50 | V |
| Repetitive Peak Reverse Voltage | VRRM | 75 | V |
| Repetitive Peak Forward Current | IFRM | 600 | mA |
| Forward Voltage | VF | | V |
| IF= 1mA | | 0.62 | |
| IF= 10mA | | 0.74 | |
| IF= 50mA | | 0.86 | |
| IF= 100mA | | 0.92 | |
| IF= 200mA | | 1.00 | |
| Reverse Current | IR | | uA |
| VR= 50V | | 0.10 | |
| VR= 50V (Tj= 150°C) | | 100 | |
| Junction Capacitance VR = 0 V, f = 1MHz | Cj | 2.5 | pF |